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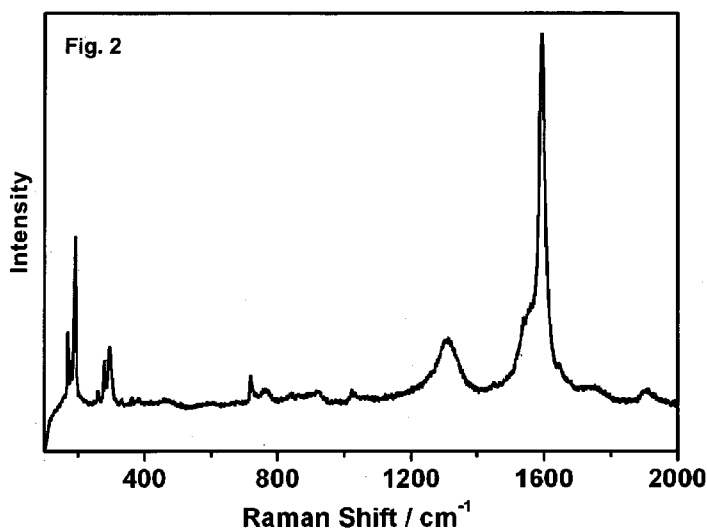
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(54) Title: METHOD OF FORMING SINGLE-WALLED CARBON NANOTUBES



(57) Abstract: The present invention relates to a method of forming single-walled carbon nanotubes. The method comprises contacting a gaseous carbon source with mesoporous TUD-1 silicate at suitable conditions. The mesoporous TUD-1 silicate comprises a metal of groups 3-13 of the Periodic Table of the Elements.